

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TPCA8025

Lithium-Ion Battery Applications

Notebook PC Applications

Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $R_{DS(ON)} = 2.7 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 80\text{S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 30 \text{ V}$)
- Enhancement mode: $V_{th} = 1.3 \text{ to } 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

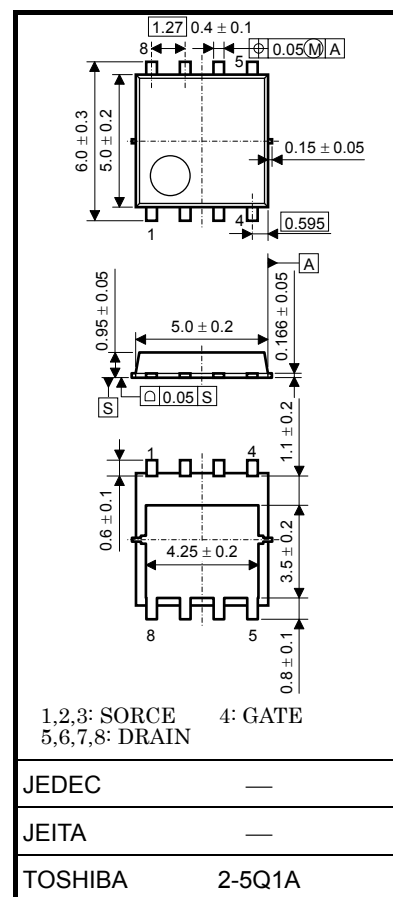
Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	30	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	A
	Pulsed (Note 1)	I_{DP}	
Drain power dissipation ($T_c = 25^\circ\text{C}$)	P_D	45	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2a)	P_D	2.8	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2b)	P_D	1.6	W
Single pulse avalanche energy (Note 3)	E_{AS}	208	mJ
Avalanche current	I_{AR}	40	A
Repetitive avalanche energy ($T_c = 25^\circ\text{C}$) (Note 4)	E_{AR}	4.5	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

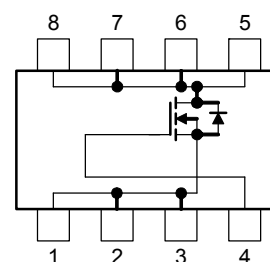
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

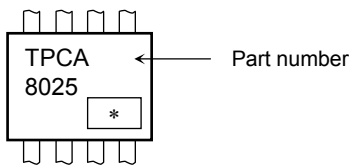
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th} (ch-c)	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th} (ch-a)	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th} (ch-a)	78.1	°C/W

Marking (Note 5)

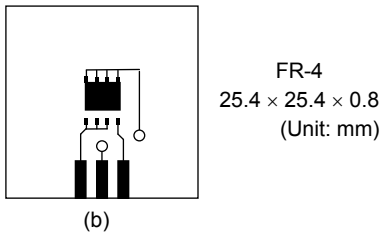
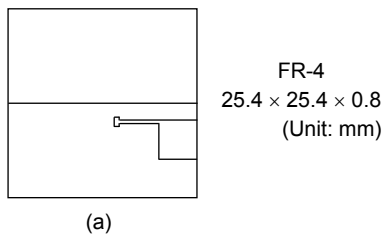


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:

(a) Device mounted on a glass-epoxy board (a)

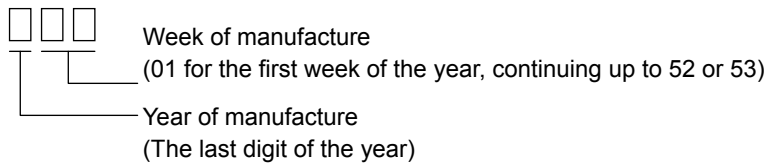
(b) Device mounted on a glass-epoxy board (b)



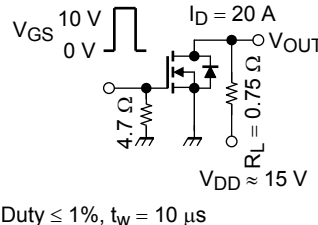
Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.1mH, R_G = 25 Ω, I_{AR} = 40 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: *Weekly code: (Three digits)

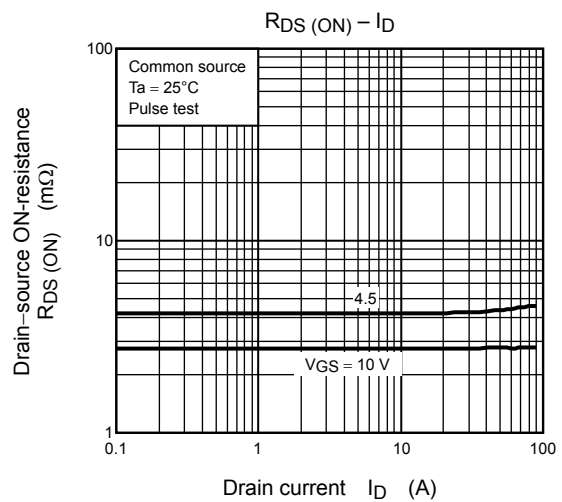
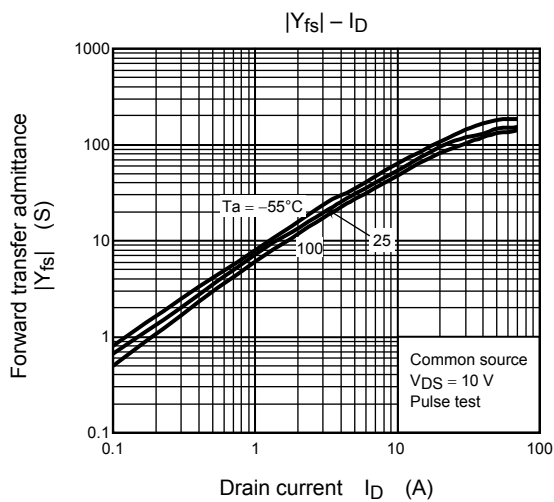
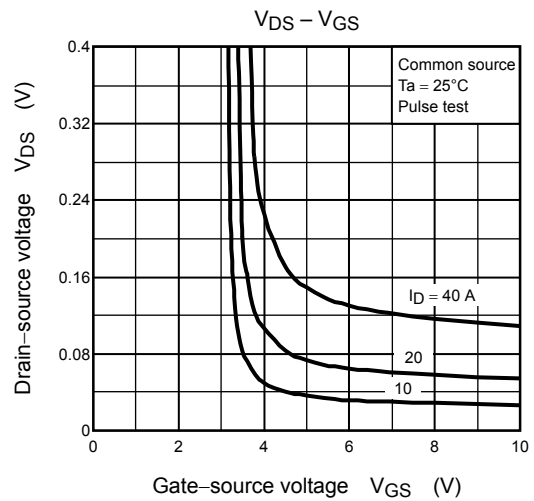
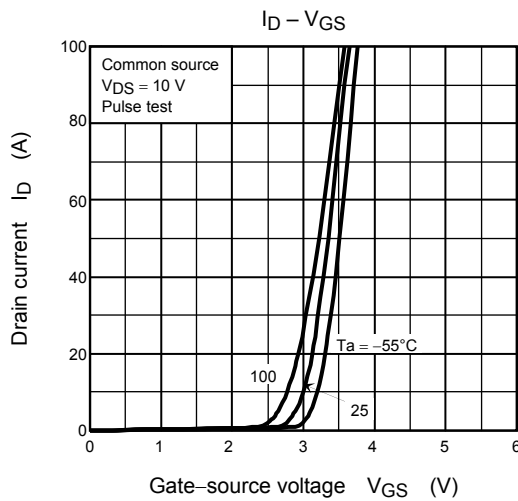
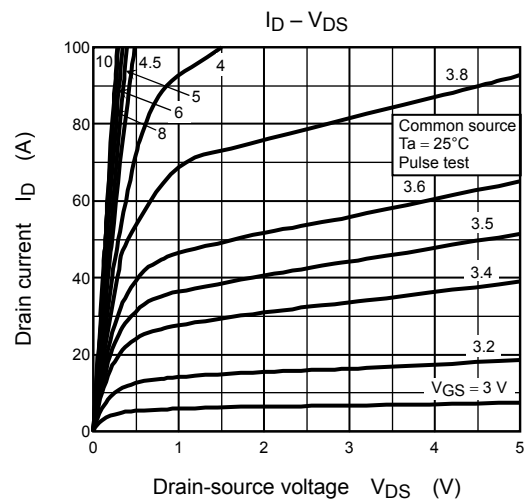
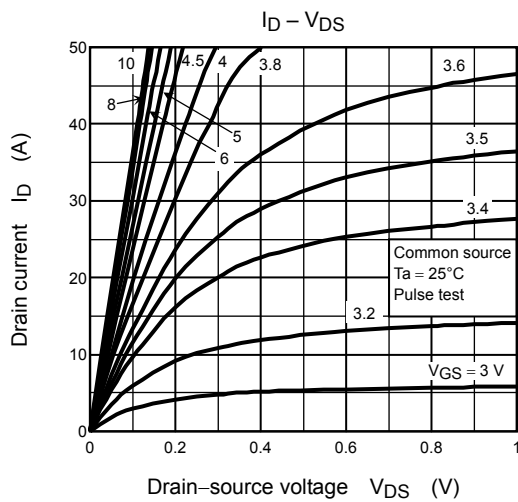


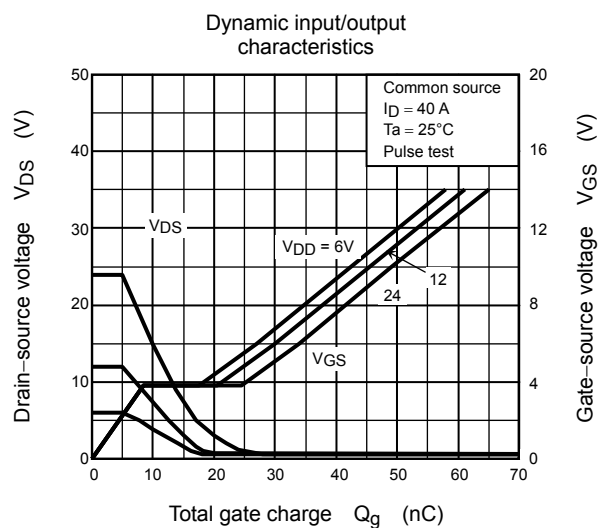
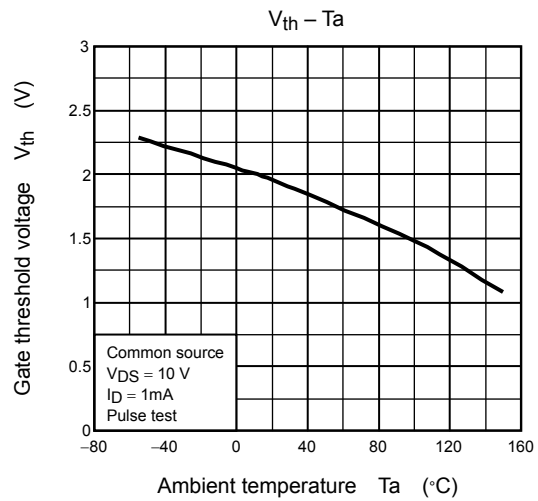
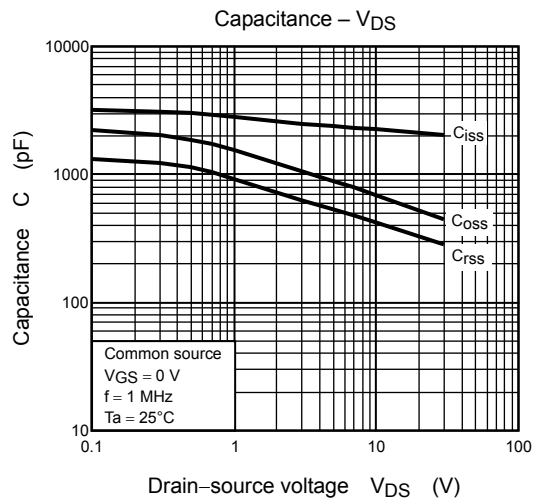
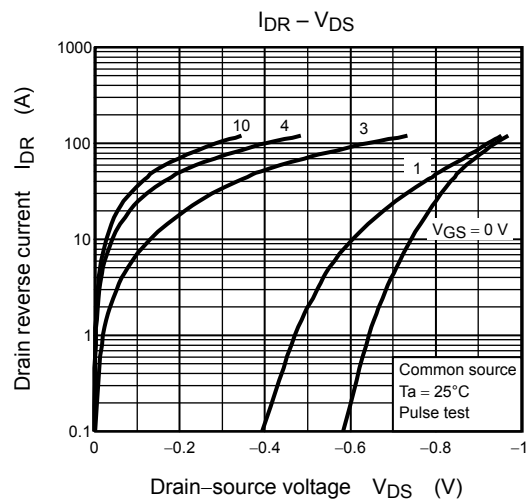
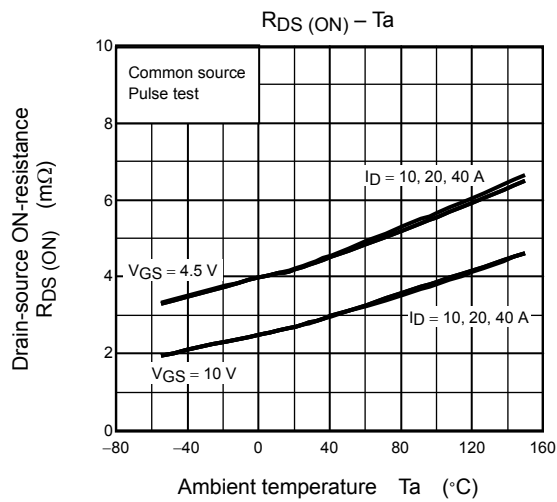
Electrical Characteristics (Ta = 25°C)

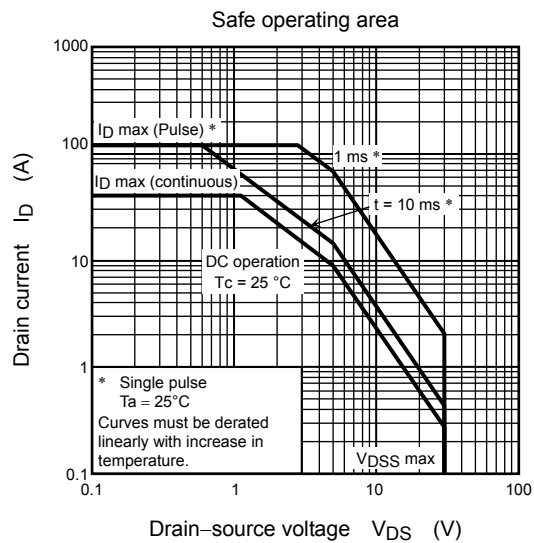
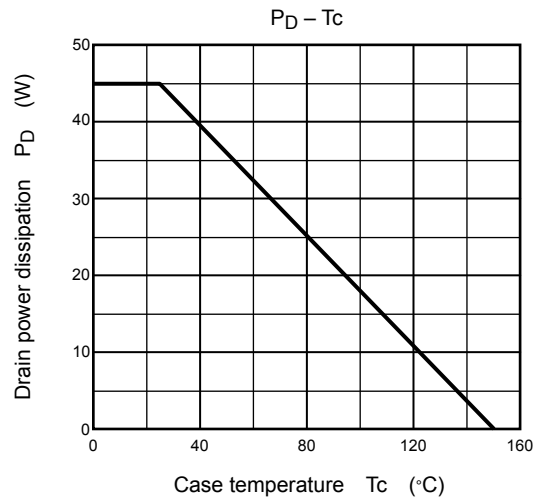
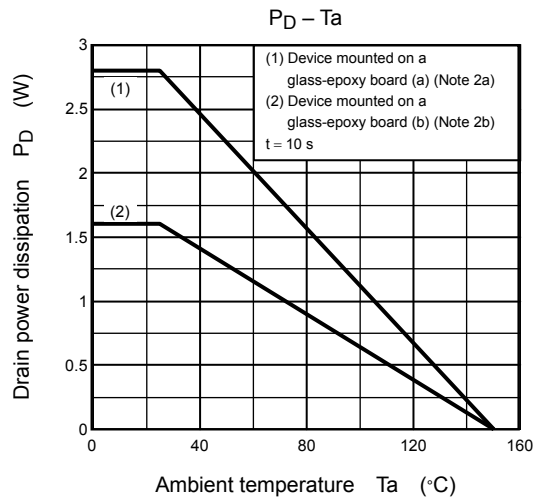
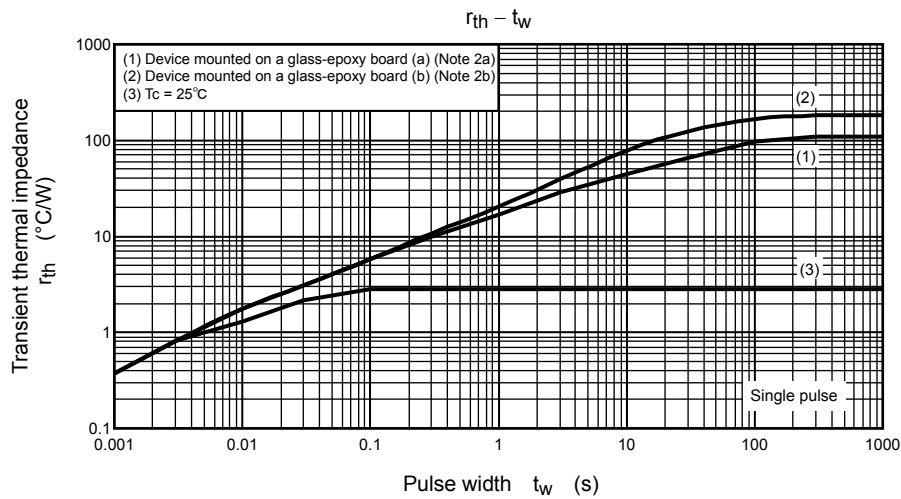
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	—	—	±100	nA
Drain cut-OFF current		I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	—	—	10	μA
Drain-source breakdown voltage		V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	30	—	—	V
		V _(BR) DSX	I _D = 10 mA, V _{GS} = −20 V	10	—	—	
Gate threshold voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	—	2.5	V
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 4.5 V, I _D = 20 A	—	4.2	6	mΩ
			V _{GS} = 10 V, I _D = 20 A	—	2.7	3.5	
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 20 A	40	80	—	S
Input capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	2200	—	pF
Reverse transfer capacitance		C _{rss}		—	430	—	
Output capacitance		C _{oss}		—	690	—	
Switching time	Rise time	t _r	 Duty ≤ 1%, t_w = 10 μs	—	12	—	ns
	Turn-ON time	t _{on}		—	22	—	
	Fall time	t _f		—	23	—	
	Turn-OFF time	t _{off}		—	74	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ 24 V, V _{GS} = 10 V, I _D = 40 A	—	49	—	nC
Gate-source charge 1		Q _{gs1}		—	8.5	—	
Gate-drain (“miller”) charge		Q _{gd}		—	16	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	120	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 40 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V







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